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ABSTRACT OF THE DISCLOSURE

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A DFB type semiconductor laser device can be readily manufactured obviating the need to form a ridge without any complicated process, and a method of manufacturing the same is described. The DFB type semiconductor laser device includes a laser substrate, a grating layer, an insulating layer and an electrode layer, which are laminated in the given order, the insulating layer including a through groove or grooves extending to the grating layer in a direction in which a resonator of the laser device is formed, the electrode layer contacting the grating layer and the clad layer.

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